

**FOR IMMEDIATE RELEASE:
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Quintessence Photonics Corporation achieves record brightness at 808nm and announces the commercialization of its proprietary BrightLase™ technology

(SYLMAR, CA) May 23, 2005 — Quintessence Photonics Corporation, a world leader in the design and manufacture of high brightness, high power semiconductor lasers, has demonstrated >6.25W from a 50um wide 808nm single emitter, in excess of 125mW per micron of emitting length. Manufactured with QPC's proprietary BrightLase™ semiconductor laser growth, processing, cleaving and coating technology, the single emitter power levels are well above the facet power densities previously reported in the 808nm regime.

"Our customer's applications are increasingly requiring the highest brightness single emitters for their solid state laser pumping, materials processing, medical, printing, and defense products. The demonstration of world record brightness levels from 808nm high power single emitters will enable Quintessence to commercialize a new line of high brightness high power semiconductor lasers." Jeffrey Ungar, Chief Executive Officer at Quintessence, commented.

About Quintessence Photonics Corporation

Quintessence Photonics Corporation is a world leader in the development and commercialization of high brightness, high power semiconductor lasers for the industrial, defense, and medical markets. Founded in the year 2000, Quintessence is vertically integrated from epitaxy through packaging and performs all critical fabrication processes at its state-of-the-art high-technology facility in the Los Angeles suburb of Sylmar, CA. For more information, please visit www.qpc.cc or contact George Lintz at (818) 833-4668 or by email at info@qpc.cc.